

GW5AS-138

Data Sheet

DS1114-1.0E, 10/24/2023

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1 General Description

GOWINSEMI GW5AS-138 devices are the 5th-generation of Arora family, with abundant internal resources, a new-architecture and high-performance DSP supporting AI operations, high-speed LVDS interfaces, and abundant BSRAM resources. At the same time, it integrates a hardcore processor RiscV AE350_SOC, self-developed DDR3, and provides a variety of packages. It is suitable for applications such as low power, high performance and compatibility designs.

GOWINSEMI provides a new generation of FPGA hardware development environment that supports FPGA synthesis, placement & routing, bitstream generation and download, etc.

1.1 Features

- Lower power consumption
 - 22nm SRAM process
 - Core Power (LV version): 0.9V / 1.0V
 - Supports dynamic on/off of clock
- Abundant basic logic cells
 - GW5AS-138 provides up to 138K LUT4s
 - Supports shadow SRAMs
- Block SRAMs with multiple modes
 - Supports Dual Port, Single Port, and Semi Dual Port
 - Supports bytes write enable
 - Supports ECC detection and error correction
- Supports MIPI D-PHY RX hard core
 - Supports MIPI DSI and MIPI CSI-2 RX
 - Up to 2.5 Gbps per MIPI

lane

- Supports up to eight data lanes and two clock lanes, with the max. transmission speed up to 20Gbps
- GPIO supports MIPI D-PHY RX
 - GPIO can be configured as MIPI DSI and MIPI CSI-2 RX interfaces
 - Up to 1.5 Gbps per MIPI lane
- High performance DSP blocks with a new architecture
 - High performance digital signal processing
 - Supports 27 x 18, 12 x 12,
 27 x 36 multiplier and 48-bit accumulator
 - Supports cascading of multipliers
 - Supports Pipeline mode and Bypass mode

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- Pre-addtion operation for filter function
- Supports barrel shifter
- A hardcore processor RiscV AE350 SOC
- A new and flexible X-channel oversampling ADC with high accuracy, no external voltage source required
 - 60dB SNR
 - 1kHz Signal Bandwidth
- Supports various SDRAM interfaces, up to DDR3 1333 Mb/s
- Multiple I/O standards
 - Hysteresis option for input signals
 - Supports drive strengths of 4mA, 8mA,12mA, 16mA, 24mA, etc.
 - Individual Bus Keeper, Pullup, Pull-down, and Open Drain options
 - Hot Socket
- 16 global clocks, 12 high-

1.2 Product Resources

- **Table 1-1 Product Resources**
- Device GW5AS-138 LUT4 138240 138240 Flip-Flop (REG) Distributed Static Random Access 1080 Memory SSRAM(Kb) Block Static Random Access Memory 6120 BSRAM(Kb) Number of BSRAMs 340 DSP (27-bit x 18-bit) 298 Maximum phase locked loop[1](PLLs) 12 Global Clocks 16 **High-speed Clocks** 24 1.25 LVDS Gbps 1333 DDR3 Mbps 2.5Gbps (RX) MIPI DPHY hard core 8 data lanes 2 clock lanes

- performance PLLs, 24 high speed clocks
- Configuration and Programming
 - JTAG configuration
 - Four GowinConfig configuration modes: SSPI, MSPI, CPU, SERIAL
 - Supports programming the SPI Flash directly in JTAG and SSPI modes; For other modes, you can program the SPI Flash using IP
 - Supports background upgrade
 - Supports bitstream file encryption and security bit settings
 - Supports configuration memory soft error recovery (CMSER). Including Basic mode and Advanced mode
 - Supports OTP. Offers a unique 64-bit DNA identifier for each device

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Device	GW5AS-138
Hard-core Processor	RiscV AE350_SOC
ADC	2
Number of GPIO banks	6
Maximum number of I/Os	312
Core voltage	0.9V/1.0V

Note!

[1] Different packages support different numbers of PLLs.

Table 1-2 Package Information and Maximum Number of User I/Os

Package	Pitch (mm)	Size (mm)	GW5AS-138
UG324A	0.8	15 x 15	222 (106)

Note!

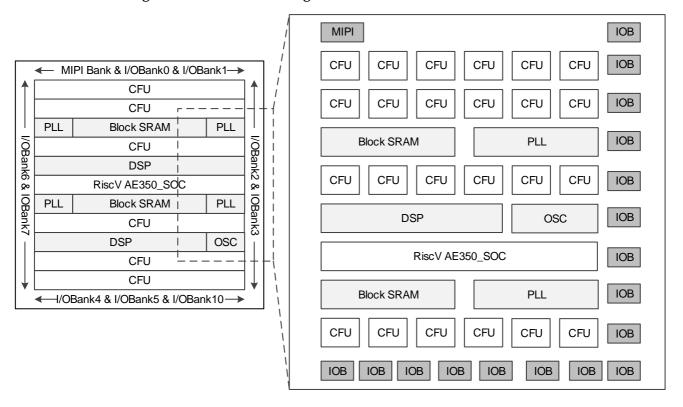
[1] The package types in this data sheet are written with abbreviations. See 4.1 Part Name for further information.

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2 Architecture

2.1 Architecture Overview

Figure 2-1 Architecture Diagram



Take GW5AS-138 as an example, see Figure 2-1 for an overview of the architecture of the GW5AS-138 devices. Please refer to Table 1-1 for device internal resources. The core of the device is an array of Configurable Logic Units (CFU) surrounded by IO blocks. Besides, BSRAMs, DSP blocks, MIPI D-PHY, ADC, PLLs, and on chip oscillators are provided.

Configurable Function Unit (CFU) is the base cell for the array of the GW5AS-138 devices. Devices with different capacities have different numbers of rows and columns. CFU can be configured as LUT4 mode, ALU mode, and memory mode. For more detailed information, see 2.2

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Configurable Function Units.

The I/O resources in the GW5AS-138 devices are arranged around the periphery of the devices in groups referred to as banks. I/O resources support multiple I/O standards, and support regular mode, SRD mode, generic DDR mode, and DDR_MEM mode. For more detailed information, see <u>2.3 Input/Output Blocks</u>.

The BSRAM is embedded as a row in GW5AS-138 devices. Each BSRAM has a maximum capacity of 36Kbits and consists of two 18Kbits BSRAMs. It supports multiple configuration modes and operation modes. For more detailed information, see 2.4 Block SRAM (BSRAM).

GW5AS-138 devices are embedded with a brand-new DSP, which can meet the high-performance digital signal processing requirements. For details, refer to 2.5 DSP Blocks..

GW5AS-138 devices provide a MIPI D-PHY hardcore supporting the "MIPI Alliance Standard for D-PHY Specification(V1.2)". For details, see <u>2.6 MIPI D-PHY</u>.

GW5AS-138 devices provide a hardcore processor RiscV AE350_SOC. For details, see <u>2.7 RiscV AE350_SOC</u>

GW5AS-138 devices integrate a new and flexible oversampling ADC. For details, see <u>2.8 ADC</u>.

GW5AS-138 devices have embedded PLL resources. PLL blocks provide the ability to synthesize clock frequencies. Frequency adjustment (multiply and division), phase adjustment, and duty cycle can be adjusted using the configuration of parameters. This series of FPGAs also have an embedded programmable on-chip clock oscillator that supports clock frequencies ranging from 1.67 MHz to 105MHz, providing clocking resources for the MSPI mode. The on-chip clock oscillator also provides programmable user clocks. For more information, see <u>2.12</u> On Chip Oscillator.

FPGA provides abundant CRUs, connecting all the resources in FPGA. For example, routing resources distributed in CFU and IOB connect resources in CFU and IOB. Routing resources can automatically be generated by Gowin software. In addition, the GW5AS-138 devices also provide abundant GCLKs, long wires (LW), global set/reset (GSR), and programming options, etc. For more details, see 2.10 Global Set/Reset (GSR), and 2.11 Programming & Configuration.

2.2 Configurable Function Units

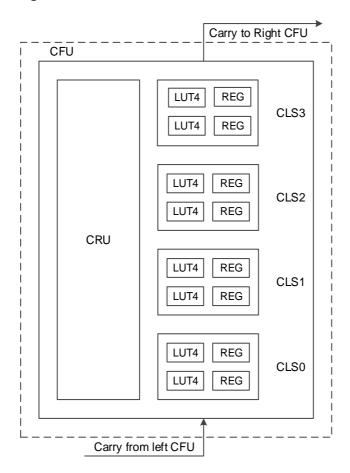
Configurable Function Units (CFUs) are the basic cells for the array of GOWINSEMI FPGA Products. Each basic cell consists of four Configurable Logic Sections (CLSs) and their routing resource Configurable Routing Units (CRUs). Each CLS includes two 4 input look-up-tables (LUTs) and two registers (REGs), as shown in Figure 2-2.

CLSs in the CFUs can be configured as basic look-up tables, arithmetic logic units, static random access memories, and read only memories according to application scenarios.

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For more details, please see <u>UG303, Arora V Configurable Function</u> <u>Unit (CFU) User Guide</u>.

Figure 2-2 CFU Structure View



2.3 Input/Output Blocks

The IOB in the GW5AS-138 devices includes IO buffer, IO logic, and its routing unit. As shown in Figure 2-3, each IOB connects to two Pins (Marked as A and B). They can be used as a differential pair or as a single end input/output.

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Differential Pair Differential Pair "True" "True" "Comp" "Comp" PAD A PAD B PAD A PAD B Buffer Pair A & B Buffer Pair A & B DO 디디 ㅁ딩 IO Logic IO Logic IO Logic IO Logic В В Routing Routing

Figure 2-3 IOB Structure View

IOB Features:

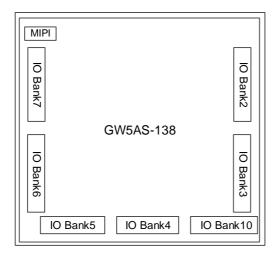
- Vccio supplied with each bank
- All banks support True differential input
- Supports multiple levels: LVCMOS, PCI, LVTTL, SSTL, HSTL, LVDS, Mini LVDS, RSDS, PPDS, BLVDS
- Input hysteresis option
- Output drive strength option
- Individual bus keeper, weak pull-up, weak pull-down, and open drain option
- Hot socket
- IO logic supports SDR mode, DDR mode, etc.

2.3.1 I/O Buffer

GW5AS-138 has six GPIO Banks (Bank2 \sim 7), a Bank for configuration (Bank 10), as shown in Figure 2-4Figure . Bank 10 can also be used as an I/O Bank.

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Figure 2-4 Bank Distribution View of GW5AS-138



Each Bank has its independent I/O power supply Vccio. Vccio can be set as 3.3V, 2.5V, 1.8V, 1.5V, 1.35V, 1.2V, or 1V.

Note!

GW5AS-138: To support SSTL, HSTL, etc., each bank also provides one independent voltage source (VREF) as the reference voltage. You can choose from the internal reference voltage of the bank (0.6V, 0.675V, 0.75V, 0.9V, and (33%,42%,50%,58%)Vcco) or the external reference voltage using any IO from the bank.

The auxiliary voltage V_{CCX} of GW5AS-138 devices supports 1.8V.

Different banks in the GW5AS-138 devices support different on-chip resistor settings, including single-ended resistor and differential resistor. Single-ended resistor is set for SSTL/HSTL I/O. Differential resistor is set for LVDS/PPDS/ RSDS input. For more details, refer to <u>UG304, Arora V Programmable IO (GPIO) User Guide</u>.

Note!

Before and during configuration, all GPIOs of the device have weak pull-up by default. The default I/O state is None after configuration is complete and it can be configured via the Gowin software. The status of configuration-related I/Os differs depending on the configuration mode.

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For the different I/O standards and configuration options, please refer to Table 2-1 and Table 2-2.

Table 2-1 Output I/O Standards and Configuration Options (GW5AS-138)

I/O output standard	Single-ended/ Differential	Bank V _{CCIO} (V)	Drive Strength (mA)	Typical Applications
LVDS25		2.5/3.3	3.5/2.5/4.5/6	High-speed point- to-point data transmission
BLVDS25		2.5/3.3	3.5/2.5/4.5/6	Multi-point high- speed data transmission
RSDS	Differential(TLV DS)	2.5/3.3	3.5/2.5/4.5/6	High-speed point- to-point data transmission
MINILVDS		2.5/3.3	3.5/2.5/4.5/6	LCD timing driver interface and column driver interface
PPLVDS		2.5/3.3	3.5/2.5/4.5/6	LCD row/column driver
LVDS25E		2.5	8/4/12/16/24	High-speed point- to-point data transmission
BLVDS25E		2.5	8/4/12/16/24	Multi-point high- speed data transmission
MLVDS25E		2.5	8/4/12/16/24	LCD timing driver interface and column driver interface
RSDS25E		2.5	8/4/12/16/24	High-speed point- to-point data transmission
LVPECL33E		3.3	8/4/12/16/24	Universal interface
HSUL12D		1.2	8/4/12	LPDDR2
HSUL12D_I		1.2	8/4/12	LPDDR2
HSTL15D_I	Differential	1.5	8/4/12/16	Memory interface
HSTL15D_II ^[4]		1.5	8/4/12/16	Memory interface
HSTL18D_I		1.8	8/4/12/16	Memory interface
HSTL18D_II		1.8	8/4/12/16	Memory interface
SSTL135D		1.35	8/4/12	Memory interface
SSTL15D		1.5	8/4/12/16	Memory interface
SSTL18D_I		1.8	8/4/12/16/24	Memory interface
SSTL18D_II		1.8	8/4/12/16/24	Memory interface
LPDDRD		1.8	8/4/12/16/24	LPDDR and Mobile DDR
LVCMOS10D		1.0E	4	Universal interface
LVCMOS12D		1.2	4/8	Universal interface
LVCMOS15D		1.5	4/8/12	Universal interface

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I/O output standard	Single-ended/ Differential	Bank V _{CCIO} (V)	Drive Strength (mA)	Typical Applications
LVCMOS18D		1.8	4/8/12/16/24	Universal interface
LVCMOS25D		2.5	4/8/12/16/24	Universal interface
LVCMOS33D		3.3	8/4/12/16/24	Universal interface
HSUL12		1.2	8/4/12	Memory interface
HSTL12_I		1.2	8/4/12	Memory interface
HSTL15_I		1.5	8/4/1216	Memory interface
HSTL15_II		1.5	8/4/12/16	Memory interface
HSTL18_I		1.8	8/4/12/16/24	Memory interface
HSTL18_II		1.8	8/4/12/16/24	Memory interface
SSTL135		1.35	8/4/12	Memory interface
SSTL15		1.5	8/4/12/16	Memory interface
SSTL18_I		1.8	8/4/12/16/24	Memory interface
SSTL18_II	Single-ended	1.8	8/4/12/16/24	Memory interface
LVCMOS10		1.0		Universal interface
LVCMOS12		1.2	4/8	Universal interface
LVCMOS15		1.5	4/8/12	Universal interface
LVCMOS18		1.8	4/8/12/16/24	Universal interface
LVCMOS25		2.5	4/8/12/16/24	Universal interface
LVCMOS33/L VTTL33		3.3	8/4/12/16/24	Universal interface
LPDDR		1.8	8/4/12/16/24	LPDDR and Mobile DDR
PCI33		3.3	8/4/12/16/24	PC and embedded system

Table 2-2 Input I/O Standards and Configuration Options (GW5AS-138)

I/O Input Standard	Single-ended/ Differential	Bank V _{CCIO} (V)	Hysteresis	Need V _{REF}
MIPI		1.2	No	No
ADC_in		2.5/1.0/1.2/1.5/1.8/3.3	No	No
LVDS25		2.5/1.0/1.2/1.5/1.8/3.3	No	No
BLVDS25		2.5/1.0/1.2/1.5/1.8/3.3	No	No
RSDS		2.5/1.0/1.2/1.5/1.8/3.3	No	No
MINILVDS	Differential	2.5/1.0/1.2/1.5/1.8/3.3	No	No
PPLVDS	Differential	2.5/1.0/1.2/1.5/1.8/3.3	No	No
HSUL12D		1.2/1.0/1.5/1.8/2.5/3.3	No	No
HSTL12D_I		1.2/1.0/1.5/1.8/2.5/3.3	No	No
HSTL15D_I		1.5/1.0/1.2/1.8/2.5/3.3	No	No
HSTL15D_II		1.5/1.0/1.2/1.8/2.5/3.3	No	No
HSTL18D_I		1.8/1.0/1.2/1.5/2.5/3.3	No	No

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I/O Input Standard	Single-ended/ Differential	Bank V _{CCIO} (V)	Hysteresis	Need V _{REF}
HSTL18D_II		1.8/1.0/1.2/1.5/2.5/3.3	No	No
SSTL135D		1.35/1.0/1.2/1.5/1.8/2.5/3. 3	No	No
SSTL15D		1.5/1.0/1.2/1.8/2.5/3.3	No	No
SSTL18D_I		1.8/1.0/1.2/1.5/2.5/3.3	No	No
SSTL18D_II		1.8/1.0/1.2/1.5/2.5/3.3	No	No
LPDDRD		1.8/1.0/1.2/1.5/2.5/3.3	No	No
LVCMOS10D		1.0/1.2/1.5/1.8/2.5/3.3	No	No
LVCMOS12D		1.2/1.0/1.5/1.8/2.5/3.3	No	No
LVCMOS15D		1.5/1.0/1.2/1.8/2.5/3.3	No	No
LVCMOS18D		1.8/1.0/1.2/1.5/2.5/3.3	No	No
HSUL12		1.2	No	Yes
HSTL12_I		1.2	No	Yes
HSTL15_I		1.5	No	Yes
HSTL15_II		1.5	No	Yes
HSTL18_I		1.8	No	Yes
HSTL18_II		1.8	No	Yes
SSTL135		1.35	No	Yes
SSTL15		1.5	No	Yes
SSTL18_I		1.8	No	Yes
SSTL18_II		1.8	No	Yes
LVCMOS10		1.0E	No	No
LVCMOS10UD12		1.2	No	No
LVCMOS10UD15		1.5	No	No
LVCMOS10UD18	Cinale ended	1.8	No	No
LVCMOS10UD25	Single-ended	2.5	No	No
LVCMOS10UD33		3.3	No	No
LVCMOS12		1.2	Yes	No
LVCMOS15		1.5	Yes	No
LVCMOS15OD10		1.0E	Yes	No
LVCMOS150D12		1.2	Yes	No
LVCMOS15UD18	-	1.8	Yes	No
LVCMOS15UD25		2.5	Yes	No
LVCMOS15UD33		3.3	Yes	No
LVCMOS18		1.8	Yes	No
LVCMOS18OD10		1.0E	Yes	No
LVCMOS180D12		1.2	Yes	No
LVCMOS180D15		1.5	Yes	No
LVCMOS18UD25		2.5	Yes	No

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I/O Input Standard	Single-ended/ Differential	Bank V _{CCIO} (V)	Hysteresis	Need V _{REF}
LVCMOS18UD33		3.3	Yes	No
LVCMOS25		2.5	Yes	No
LVCMOS25UD33		3.3	Yes	No
LVCMOS33/LVTT L33		3.3	Yes	No
LVCMOS33OD25		2.5	Yes	No
LPDDR		1.8	Yes	No
PCI33		3.3	Yes	No
VREF1_DRIVER		1.8/1.2/1.35/1.5	No	Yes

2.3.2 I/O Logic

Figure 2-5 shows the I/O logic output of GW5AS-138 devices.

Figure 2-5 I/O Logic Output

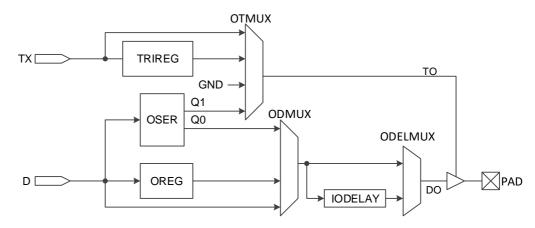
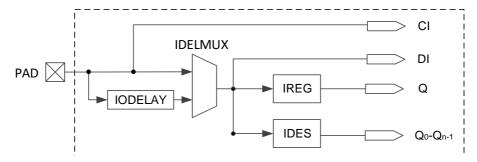


Figure 2-6 shows the I/O logic input of the GW5AS-138 devices.

Figure 2-6 I/O Logic Input



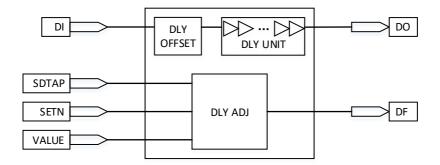
Descriptions of the I/O logic modules of GW5AS-138 devices are presented below.

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Delay Modules

See Figure 2-7 for an overview of the IODELAY. Each I/O of GW5AS includes IODELAY, providing a total of 256 (0~255) delays, with a single-step delay time of about 12.5ps. The total IODELAY time is DLYOFFSET+DLY UNIT*SDTAP.

Figure 2-7 IODELAY



There are three ways to control the delay:

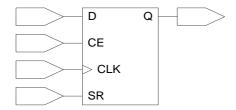
- Static control.
- Dynamic control, which can be combined with logic function circuits to achieve dynamic delay adjustment.
- Adaptive control.

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I/O Register

See Figure 2-8 for the I/O register in GW5AS-138 devices. Each I/O of the GW5AS-138 devices provides one input register (IREG), one output register (OREG), and one tristate Register (TREG).

Figure 2-8 Diagram of I/O registers



Note!

- CE can be either active ow (0: enable) or active high (1: enable).
- CLK can be either rising edge trigger or falling edge trigger.
- SR can be either synchronous/asynchronous SET or RESET or disable.
- The registers can be programmed as registers(DFFs) or latches.

De-serializer DES and Serializer SER

The GW5AS-138 devices support serialization and deserialization of various ratios, as shown in the following table:

Table 2-3 DES/SER Ratios Supported by the GW5AS-138 devices

	Ratios Supported
Input logic	1:2 / 1:4 / 1:7 / 1:8 / 1:10 / 1:14 / 1:16 / 1:32
Output logic	2:1 / 4:1/ 7:1 / 8:1 / 10:1 / 16:1

2.3.3 I/O Logic Modes

The I/O Logic in GW5AS-138 devices supports several modes. In each operation, the I/O (or I/O differential pair) can be configured as output, input, and INOUT or tristate output (output signal with tristate control).

For further details about the I/O logic modes, refer to <u>UG304, Arora V</u> Programmable IO (GPIO) User Guide.

2.4 Block SRAM (BSRAM)

2.4.1 Introduction

GW5AS-138 devices provide abundant block SRAM resources. These memory resources are distributed throughout the FPGA array in the form of rows. Therefore, they are called block static random access memories (BSRAMs). Up to 36Kbits can be configured for each BSRAM. There are five operation modes: Single Port mode, Dual Port mode, Semi Dual Port mode, Semi Dual Port mode with ECC function, and ROM mode.

An abundance of BSRAM resources provide a guarantee for the user's high-performance design. BSRAM's features:

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- Up to 36Kbits per BSRAM
- Clock frequency up to 380MHz
- Supports Single Port mode
- Supports Dual Port mode
- Supports Semi Dual Port Mode
- Supports ECC detection and error correction Function
- Supports ROM Mode
- Data width up to 72bits
- Dual Port and Semi-Dual Port support independent clocks and independent data width
- Read mode supports Register Output and Bypass Output
- Write mode supports Normal and Write-Through

2.4.2 Configuration Mode

BSRAMs in the GW5AS-138 devices support various data widths. See Table 2-4.

Capacity	Single Port Mode	Dual Port Mode	Semi Dual Port Mode	Semi Dual Port Mode with ECC Function	Read Only Mode
	16K x 1	16K x 1	16K x 1	_	16K x 1
	8K x 2	8K x 2	8K x 2	_	8K x 2
16Khita	4K x 4	4K x 4	4K x 4	_	4K x 4
16Kbits	2K x 8	2K x 8	2K x 8	_	2K x 8
	1K x 16	1K x 16	1K x 16	_	1K x 16
	512 x 32	_	512 x 32	_	512 x 32
	2K x 9	2K x 9	2K x 9	_	2K x 9
18Kbits	1K x 18	1K x 18	1K x 18	_	1K x 18
	512 x 36	_	512 x 36	_	512 x 36
36Kbits	_	_	_	512 x 72	_

Single Port Mode

In the single port mode, BSRAM can write to or read from one port at one clock edge. It supports 2 read modes (Bypass and Pipeline) and 2 write modes (Normal mode and Write-Through mode). In Normal-Write Mode, the written data will be stored in the internal memory array. In Write-Through Mode, the written data will not only be stored in the internal memory array, but also be written to the output of BSRAM. When the output register is Bypassed, the new data will show at the same write clock rising edge.

For more information on single port mode, please refer to <u>UG300</u>, Arora V BSRAM & SSRAM User Guide.

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Dual Port Mode

BSRAM supports Dual Port mode. It supports 2 read modes (Bypass and Pipeline) and 2 write modes (Normal and Write-Through). The applicable operations are as follows:

- Two independent read, reading data from any given address.
- Two independent write, writing data to any address that is different.
- An independent read and an independent write at different clock frequencies.

Note!

- In Dual-port mode, Port A and Port B can read from or write to the same address. Null or repeated reads do not damage the storage module.
- In Dual-port mode, when Port A and Port B write to the same address at the same time, the dual ports writing fail at the same time.
- When Port A reads, Port B writes, and they access the same address, the write port succeeds, but the read port fails, and the output data is unknown. BSRAM contents are the values from the write port.

Dual Port supports independent read/write clocks and independent read/write data width. For more information on dual port mode, please refer to *UG300*, *Arora V BSRAM & SSRAM User Guide*.

Semi Dual Port Mode

Semi-dual ports support independent read/write operations in the form of A port write-only ("Normal") and B port read-only. When Port A reads, Port B writes, and they access the same address, the write port succeeds, but the read port fails, and the output data is unknown. BSRAM contents are the values from the write port.

Semi-dual Port supports independent read/write clocks and independent read/write data width. For more information on semi dual port mode, please refer to <u>UG300</u>, <u>Arora V BSRAM & SSRAM User Guide</u>.

Semi Dual Port Mode with ECC Function

Semi-dual ports with ECC Function support independent read/write operations in the form of A port write-only and B port read-only. Independent read/write data width is also supported. This mode provides ECC function. For more information on this mode, please refer to <u>UG300</u>, <u>Arora V BSRAM & SSRAM User Guide</u>.

Read Only Mode

BSRAM can be configured as ROM. The ROM can be initialized during the device configuration stage, and the ROM data needs to be provided in the initialization file. Initialization completes during the device power-on process.

Each BSRAM can be configured as one 16 Kbits ROM. For more information on read only mode, please refer to <u>UG300, Arora V BSRAM & SSRAM User Guide</u>.

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2.4.3 Data Width Configuration

BSRAMs in the GW5AS-138 devices support independent data width for read/write operations. In Dual Port mode, Semi Dual Port mode, and Semi Dual Port mode with ECC function, the data width for Port A and Port B can be different. For the data width supported by Port A and Port B, see Table 2-5, Table 2-6, and Table 2-7.

Table 2-5 Read/Write Data Width Configuration in Dual Port Mode

Capacity	Port B	Port A						
		16K x 1	8K x 2	4K x 4	2K x 8	1K x 16	2K x 9	1K x 18
16Kbits	16K x 1	Yes	Yes	Yes	Yes	Yes	N/A	N/A
	8K x 2	Yes	Yes	Yes	Yes	Yes	N/A	N/A
	4K x 4	Yes	Yes	Yes	Yes	Yes	N/A	N/A
	2K x 8	Yes	Yes	Yes	Yes	Yes	N/A	N/A
	1K x 16	Yes	Yes	Yes	Yes	Yes	N/A	N/A
18Kbits	2K x 9	N/A	N/A	N/A	N/A	N/A	Yes	Yes
	1K x 18	N/A	N/A	N/A	N/A	N/A	Yes	Yes

Table 2-6 Read/Write Data Width Configuration in Semi Dual Port Mode

	Port A											
Capacity Port	Port B	16K x 1	8K x	4K x	2K x	1K x 16	512x 32	2K x	1K x 18	512 x 36	1K x 36	512 x 72
16Kbits	16K x 1	Yes	Yes	Yes	Yes	Yes	Yes	N/A	N/A	N/A	N/A	N/A
	8K x 2	Yes	Yes	Yes	Yes	Yes	Yes	N/A	N/A	N/A	N/A	N/A
	4K x 4	Yes	Yes	Yes	Yes	Yes	Yes	N/A	N/A	N/A	N/A	N/A
	2K x 8	Yes	Yes	Yes	Yes	Yes	Yes	N/A	N/A	N/A	N/A	N/A
	1K x 16	Yes	Yes	Yes	Yes	Yes	Yes	N/A	N/A	N/A	N/A	N/A
	512 x 32	Yes	Yes	Yes	Yes	Yes	Yes	N/A	N/A	N/A	N/A	N/A
18Kbits	2K x 9	N/A	N/A	N/A	N/A	N/A	N/A	Yes	Yes	Yes	N/A	N/A
	1K x 18	N/A	N/A	N/A	N/A	N/A	N/A	Yes	Yes	Yes	N/A	N/A

Table 2-7 Read/Write Data Width Configuration in Semi Dual Port Mode with ECC Function

Capacity	Port B	Port A		
			512 x 72	
36Kbits	512 x 72	N/A	*	

2.4.4 ECC

The BSRAM of GW5AS-138 has a built-in ECC hardcore module,

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which is mainly used for data detection and correction during data transfer and storage. ECC features are as follows:

- ECC error detection and correction only supported in SDP 512 x 64 mode
- Supports 1-bit error correction and 2-bit error alarm in 64-bit SRAM data
- 72-bit ECC module contains 64-bit data bits and 8-bit parity bits;
- Bit 31 and bit 63 support 1-bit and 2-bit error injection

2.4.5 Byte-enable

BSRAM supports the byte_enable function- only the selected byte can be written. The byte_enable function is used for writing only and is available when the bit width is 16/18, 32/36. Read/write enable ports (WREA, WREB), and byte parameter options can be used to control the BSRAM write operation.

2.4.6 Synchronous Operation

- All the input registers of BSRAM support synchronous write.
- The output register can be used as a Pipeline register to improve design performance.
- The output registers can be Bypassed.

2.4.7 BSRAM Operation Modes

BSRAM supports four different operations, including two read operations (Bypass and Pipeline) and two write operations (Normal and Write-Through).

Read Mode

Read data from the BSRAM via output registers or without using the registers.

PIPELINE

When reading data, the data is synchronously read out via the output register according to the clock beat. This mode supports up to 72-bit data width.

BYPASS

In this mode, the output register is not used. When reading data, the data is directly sent to the output port.

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AD [**Pipeline** Input Memory DI [DO (Register Register Array WRE CLK OCE ADB Input CLKA Register Input Memory CLKB Register Array ADA Pipeline Register -OCEB DOB DIA ADA Input Input ADB Register WREB WREA Register Memory Array CLKA CLKB Pipeline Pipeline Register OCEB Register OCEA DOA DOB

Figure 2-9 Pipeline Mode in Single Port, Dual Port, and Semi-Dual Port Mode

Write Mode

NORMAL

In this mode, when the user writes data to one port, and the output data of this port does not change. The data written in will not appear at the read port.

WRITE-THROUGH

In this mode, when the user writes data to one port, and the data written in will also appear at the output of this port.

2.4.8 Clock Operations

Table 2-8 lists the clock operations in different BSRAM modes:

Table 2-8 Clock Operations in Different BSRAM Modes

Clock Operations	BSRAM Mode
------------------	------------

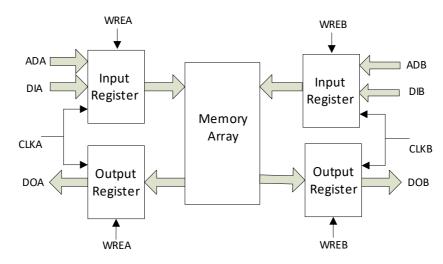
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	Dual Port Mode	Semi Dual Port Mode	Single Port Mode
Independent Clock Mode	Yes	No	No
Read/Write Clock Mode	Yes	Yes	No
Single Port Clock Mode	No	No	Yes

Independent Clock Mode

Figure 2-10 shows the independent clocks in dual port mode with each port with one clock. CLKA controls all the registers at Port A; CLKB controls all the registers at Port B.

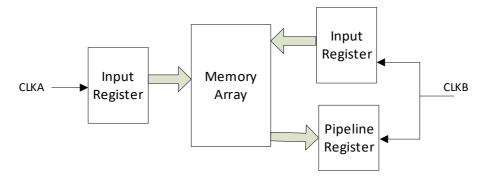
Figure 2-10 Independent Clock Mode



Read/Write Clock Operation

Figure 2-11 shows the read/write clock operations in the semi-dual port mode with one clock at each port. The write clock (CLKA) controls Port A data inputs, write address and read/write enable signals. The read clock (CLKB) controls Port B data output, read address, and read enable signals.

Figure 2-11 Read/Write Clock Mode

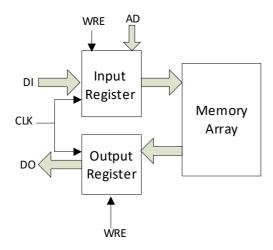


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Single Port Clock Mode

Figure 2-12 shows the clock operation in single port mode.

Figure 2-12 Single Port Clock Mode



2.5 DSP Blocks

GW5AS-138 devices provide brand new DSP resources. This DSP solution can meet user demands for high performance digital signal processing design, such as FIR, FFT, etc. DSP blocks have the advantages of stable timing performance, high resource utilization, and low power consumption.

The features of DSP are as follows.

- Can be configured as 12 x 12, 27 x 28, and 27 x 36 signed multipliers
- 48-bit arithmetic logic unit(ALU)
- Multipliers cascading to support wider data
- Barrel Shifter
- Adaptive filtering through signal feedback
- Supports Pipeline mode and Bypass mode.
- All operands for arithmetic operation are signed numbers
 Each DSP consists of three main parts:
- PADD;
- PipelineMULT;
- ALU

2.5.1 PADD

Each DSP features one PADD(pre-adder) for implementing pre-addition, pre-subtraction, and shifting.

PADD locates at the first stage with two inputs:

26-bit input C;

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Parallel 26-bit input A or SIA.
 Each input end supports Pipeline mode and Bypass mode.

2.5.2 MULT

Each DSP block has one 27 x 18 multiplier M0 and one 12 x 12 multiplier M1. The multipliers are located after the pre-adders to implement multiplication operations, and both the inputs and outputs support register mode and Bypass mode.

Multiplier M0 can be configured as:

- One 27 x 18 multiplier
- One 12 x 12 multiplier
- Two DSPs can form a 27 x 36 multiplier

Multiplier M1 can only be configured as one 12 x 12 multiplier.

When multiplier M0 and multiplier M1 are both configured as a 12 x 12 multiplier and the ALU is enabled, 12 x 12 SUM mode can be achieved.

2.5.3 ALU

Each DSP has one four-input 48-bit ALU, which can further enhance MULT's functions. Register mode and Bypass mode are supported both in the inputs and outputs. The ALU supports the addition/subtraction operations of multiplier M0 output, multiplier M1 output (48bit operand D), ALU cascade input CASI and ALU output feedback, or static PRE_LOAD value.

2.5.4 Operating Mode

Based on control signals, DSP can be configured as different operation modes. Operation Modes:

- Multiplier
- Accumulator
- MULTADDALU

For more information on DSP Blocks, see <u>UG305</u>, <u>Arora V Digital</u> <u>Signal Processing (DSP) User Guide</u>.

2.6 MIPI D-PHY

2.6.1 MIPI D-PHY RX(GW5AS-138)

GW5AS-138 provides a MIPI D-PHY RX hardcore supporting the "MIPI Alliance Standard for D-PHY Specification(V1.2)". The dedicated D-PHY core supports MIPI DSI and CSI-2 mobile video interfaces for cameras and displays. The main features are as follows:

- High Speed RX at up to 20 Gbps (eight data lanes).
- One MIPI Quad supports up to four data lanes and one clock lane.
- Bidirectional Low-power (LP) mode at up to 10Mbps per lane

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- Built-in HS Sync, bit and lane alignment
- 1:8 and 1:16 deserialization modes to FPGA fabric's user interface
- Supports MIPI DSI and MIPI CSI-2 link layers

For more information on Gowin MIPI D-PHY RX, pleae refer to *UG296, Arora V Hardened MIPI D-PHY User Guide.*

2.7 RiscV AE350_SOC

The GW5AS series FPGA products are embedded with RiscV AE350 SOC, which has the following advantages:

- Hardcore unit, which improves the MCU speed and saves FPGA logic resources.
- The reserved APB and AHB Slave buses extend to FPGA logic, which allows for flexible extension of MCU peripherals.
- The reserved AHB Master bus extends to the FPGA logic, which can access the MCU's built-in ILM and DLM, increasing the FPGA storage resources.

The RiscV AE350_SOC mainly consists of the core system, the memory system and the bus peripheral system.

- The core system includes the RISC-V core, PLIC, PLMT, debug system, clock gating, clock system, reset system, I-Cache, D-Cache, ILM, and DLM.
- The memory system includes instruction memory and data memory.
- The bus peripheral system includes AHB bus peripherals and APB bus peripherals. AHB bus peripherals include 64-bit Extended AHB Master, 32-bit Extended AHB Slave, AHB2APB Bridge. APB bus peripherals include I2C, PIT, SPI, UART1, UART2, GPIO, WDT, RTC, SMU, DMAC, 32-bit Extended APB Slave.

Main Features

- 5-stage in-order execution pipeline
- Frequency: Max. 800MHz
- Machine mode, Supervisor mode and User mode
- Hardware multiplier and divider; hardware performance monitors; hardware stack protection extension; memory management; physical memory protection entries, etc.
- 32KB I-Cache and D-Cache, LRU algorithm supported
- 64KB ILM and DLM embedded
- Instruction memory can be addressed up to 256MB and data memory up to 2GB
- Built-in PLMT, UART, PIT, WDT, RTC, GPIO, I2C, SPI and other peripheral functions

DMA

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For further information about RiscV AE350_SOC, please refer to the manuals as below:

- MUG1030, Gowin RiscV_AE350_SOC Quick Development Manual
- MUG1031, Gowin RiscV_AE350_SOC Hardware Design Manual
- MUG1032, Gowin RiscV_AE350_SOC DSP Software Programming Manual
- MUG1029, Gowin RiscV AE350 SOC Software Programming Manual
- MUG1026, Gowin RiscV_AE350_SOC RDS Software Installation Guide
- MUG1025, Gowin RiscV_AE350_SOC RDS Software Manual

2.8 ADC

The GW5AS-138 devices integrate a new flexible analog interface as a temperature and power sensor. When combined with the programmable logic capability of the FPGA, the sensor can address the data acquisition and monitoring requirements for temperature and power monitoring.

Highlights of the sensor architecture include:

- On-chip reference, no off-chip voltage reference required
- 60dB SNR
- 10-bit oversampling @ 2MHz
- 1kHz Signal Bandwidth
- two dedicated analog channels, able to detect input signals from GPIO at the same time
- On-chip temperature (±4°C max error) and voltage (±1% max error) sensors
- Continuous access to ADC measurements

The sensor optionally uses an on-chip reference circuit (±1%), thereby eliminating the need for any external active components for basic on-chip monitoring of temperature and power supply rails.

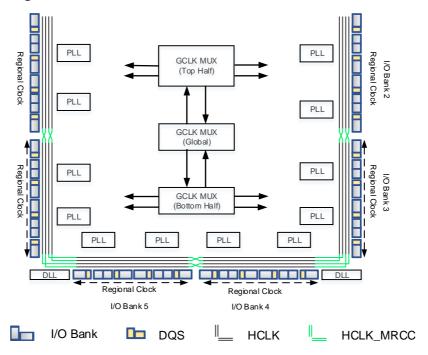
For more information on ADC, see <u>UG299, Arora V Analog to Digital</u> Converter (ADC) User Guide.

2.9 Clock

The clock resources and wiring are critical for high-performance applications in FPGA. GW5AS-138 devices provide the global clock network (GCLK) which connects to all the registers directly. In addition to the GCLK, PLL, HCLK, DDR memory interface, and DQS, etc. are also provided.

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Figure 2-13 Clock resource



Please refer to 2.9.1 ~ 2.9.4 for a brief introduction. For further detailed information on the GCLK, HCLK, DDR memory interface, and DQS, see *UG306*, *Arora V Clock User Guide*.

2.9.1 Global Clock

GW5AS series FPGA products provide 16 global clocks. The clock source of GCLK comes from dedicated clock pins, PLL output, HCLK output and common wiring resources. Dedicated clock input pins offer better clock performance and enable global driving.

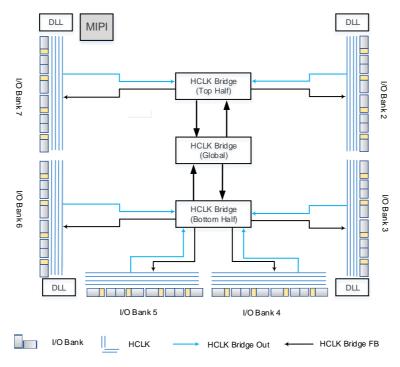
2.9.2 HCLK

HCLK is the high-speed clock with low jitter and low skew. It can support high-performance data transfer and is mainly suitable for source synchronous data transfer protocols. One bank supports 4 HCLKs, as

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shown in Figure 2-14.

Figure 2-14 GW5AS HCLK Distribution



HCLK can provide users with the function modules as follows:

- Dynamic high-speed clock enable module. Able to dynamically turn on/off the high-speed clock signal.
- High speed clock frequency division module, generating a divided clock of the input clock. Used in the IO logic mode.
- Dynamic high speed clock selector.
- Dynamic delay adjustment module, producing the clock signal for the dedicated clock pin input.
- The HCLK bridge module is able to send HCLK clock signals to any of the Banks. In addition, the HCLK clock signal can span to the clock tree of the adjacent IO Bank after entering from the IO Bank.

Note!

For high speed signals of the same source, it is recommended to put them in the same IO Bank to achieve a minimum skew between signals.

2.9.3 Phase-locked Loop

PLL (Phase-locked Loop) is one kind of a feedback control circuit. The frequency and phase of the internal oscillator signal is controlled by the external input reference clock.

The PLL module of the GW5AS series FPGA products can provide synthesizable clock frequencies. Frequency adjustment (multiply and division), phase adjustment, and duty cycle adjustment can be achieved by configuring the parameters.

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The features of the PLL module of the GW5AS series FPGA products are as follows:

- Supports seven clock outputs
- Integer PLL, the first clock output and feedback clock output support 1/8 fractional output division
- Supports phase shift and duty cycle adjustment
- Frequency Lock detection
- Supports spread spectrum clock generation (IP required)
- VCO frequency range: 800 MHz ~ 2000 MHz
- 13k devices' CLKIN frequency range: 10 MHz ~ 400 MHz.

2.9.4 DDR Memory Interface Clock Management DQS

The DQS module of the GW5AS-138 devices provides the following features to support the clock requirements of the DDR memory interface:

- Receive DQS input, sort out waveform and shift 1/4 phase
- Provide a read / write pointer for input buffer
- Provide valid data for internal logic
- Provide DDR output clock signal
- Support DDR3 write voltage control

The DQS module supports multiple operating modes to meet the needs of different I/O interfaces.

2.9.5 Long Wire

As a supplement to CRU, the GW5AS-138 devices provide another routing resource- Long Wire, which is suitable for clock, clock enable, set/reset, or other high fan out signals.

2.10 Global Set/Reset (GSR)

A global set/rest (GSR) network is built in the GW5AS series of FPGA Product. There is a direct connection to core logic. It can be used as asynchronous/synchronous set. The registers in CFU and I/O can be individually configured to use GSR.

2.11 Programming & Configuration

The GW5AS-138 devices support SRAM configuration. Each time the device is powered on, the bitstream needs to be downloaded to configure the device. Of course, you can also save the configuration data in an external Flash. After power-up, the GW5AS device loads configuration data from the external Flash into the SRAM.

Besides JTAG, the GW5AS-138 devices also support GOWINSEMI's own GowinCONFIG configuration mode: SSPI, MSPI, CPU, SERIAL. The FPGAs also support background programming, datastream file encryption and security bit setting, SEU detection and error correction, and OTP. For

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more information, please refer to <u>UG704, Arora V FPGA Products</u> <u>Programming and Configuration User Guide</u>.

Background Upgrade

GW5AS series of FPGAs support background upgrade by JTAG/SSPI/QSSPI or UserLogic, that is, the device supports programming the embedded Flash or the external Flash without affecting the existing working state, the device can work normally according to the original configuration during the programming process. And after the programming is completed, trigger RECONFIG_N with a low level to complete the online upgrade. This feature applies to the applications requiring long online time and irregular upgrades.

Bitstream File Encryption & Security Bit Setting

GW5AS-138 devices support bitstream data encryption with 128-bit AES encryption algorithm. At the same time, GOWINSEMI adds CRC and sets security bits in the bitstream file of FPGA products by default in order to guarantee the safe and accurate transmission of configuration data. During the data configuration process, the input data is verified in real time for errors, and the device cannot be woken up by incorrect data. After the configuration of the bitstream with security bit is complete, data readback cannot be performed.

CMSER

The configuration SRAM of GW5AS-138 devices supports configuration memory soft error recovery (CMSER), which are mainly used for data detection and correction of the FPGA configuration data and are disabled by default. The features are as follows:

- Supports ECC and CRC error detection and correction. Turning on the auto-on mode after wakeup according to the user configuration or using the user design logic control to turn on/off error detection and correction
- ECC supports 1-bit error location report and error correction and 2-bit error alarm per 64-bit SRAM data
- CRC supports any bit error alarm
- Supports 1-bit error injection at any position, one error per 64-bit SRAM data
- The detection and error correction function of SRAM in this storage area will be automatically turned off when the user turns on the SSRAM storage function

OTP

GW5AS-138 devices provide a 128-bit OTP space and support onetime programming. Bit0 ~ Bit31 is the user space, which can be used to store security and other important information. Bit32~Bit95 is the DNA space, which stores the 64-bit unique identification information of the device.

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2.12 On Chip Oscillator

There is an internal oscillator in each of the GW5AS-138 devices. During the configuration process, it can provide a clock for the MSPI mode. The on-chip oscillator also provides a clock resource for user designs. Up to 64 clock frequencies can be obtained by setting the parameters. The following formula is employed to get the output clock frequency:

fout=210MHz/Param.

Note!

"Param" is the configuration parameter. It is 3 or an even number between 2 and 126.

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3 AC/DC Characteristic

Note!

You should ensure GOWINSEMI® products are always used within recommended operating conditions and range. Data beyond the working conditions and range are for reference only. GOWINSEMI® does not guarantee that all devices will operate as expected beyond the standard operating conditions and range.

3.1 Operating Conditions

3.1.1 Absolute Max. Ratings

Table 3-1 Absolute Max. Ratings

Name	Description	Min.	Max.
FPGA Logic			
V _{CC}	Core voltage	-0.5V	1.05V
V _{CCIO}	I/O Bank voltage	-0.5V	3.75V
V _{CCX}	Auxiliary voltage	-0.5V	1.98V
V _{CC_REG}	Regulator voltage	-0.5V	1.98V
	Single-ended input	-0.4V	3.75V
V _{IN}	Differential input	-0.4V	2.625V
MIPI			
V_{dda}	Analog core power supply	-0.5V	1.05V
V _{ddx}	Analog high voltage power supply	-0.5V	1.98V
Temperature			
Storage Temperature	Storage Temperature	-65 °C	+150℃
Junction Temperature	Junction Temperature	-40 °C	+125℃

3.1.2 Recommended Operating Conditions

Table 3-2 Recommended Range^[1]

Name	Description	Min.	Max.
V _{CC}	Core voltage	0.87V	1.0V

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Name	Description	Min.	Max.
V _{CCIO}	I/O Bank voltage	1V	3.465V
V _{CCX}	Auxiliary voltage	1.71V	1.89V
V _{CC_REG} ^[2]	Regulator voltage	1.14V	1.89V ^[2]
MIPI			
V_{dda}	Analog core power supply	0.87V	1.0V
V _{ddx}	Analog high voltage power supply	1.71V	1.89V
Temperature			
Тусом	Junction temperature Commercial operation	0 ℃	+85 °C
T _{JIND}	Junction temperature Industrial operation	-40℃	+100℃

Note!

- [1] For the power supply information for different packages, please refer to UG1107-GW5AS-138 Pinout.
- [2] The higher the VCC_REG voltage, the higher the power consumption.

3.1.3 Power Supply Ramp Rates

Table 3-3 Power Supply Ramp Rates

Name	Description	Min.	Тур.	Max.	
V _{cc} Ramp	Power supply ramp rates	0.02mV/µs	TBD	50mV/µs	

3.1.4 Hot Socket Specifications

Table 3-4 Hot Socket Specifications

Name	Description	Condition	I/O	Max.
I _{HS}	Input or I/O leakage current	V _{IN} =V _{IL} (MAX)	I/O	150uA
I _{HS}	Input or I/O leakage current	V _{IN} =V _{IL} (MAX)	TDI, TDO, TMS,TCK	120uA

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3.1.5 POR Specifications

Table 3-5 POR Paramrters

Name	Description	Name	Тур.
POR Voltage		V_{CC}	0.72V
	Power on reset voltage	V _{CCX}	1.5V
		V _{CCIO} (Bank10)	1.04V

3.2 ESD performance

Table 3-6 GW5AS ESD - HBM

Device	НВМ
GW5AS-138	HBM > 1000V

Table 3-7 GW5AS ESD - CDM

Device	CDM
GW5AS-138	CDM > 250V

3.3 DC Characteristics

3.3.1 DC Electrical Characteristics over Recommended Operating Conditions

Table 3-8 DC Electrical Characteristics over Recommended Operating Conditions

Name	Description	Condition	Min.	Тур.	Max.
I. I.	Input or I/O leakage	V _{CCO} <v<sub>IN<v<sub>IH(MAX)</v<sub></v<sub>	-	-	210uA
I _{IL} ,I _{IH}	input of 1/O leakage	0V <v<sub>IN<v<sub>CCO</v<sub></v<sub>	-	-	10uA
		0 <v<sub>IN<0.7V_{CCO}. Pull Strength=Strong</v<sub>	-	-	-250uA
I _{PU}	I/O Active Pull-up Current	0 <vin<0.7vcco, pull="" strength="Medium</td"><td>-</td><td>-</td><td>-150uA</td></vin<0.7vcco,>	-	-	-150uA
		0 <vin<0.7vcco, pull="" strength="Weak</td"><td>-</td><td>-</td><td>-50uA</td></vin<0.7vcco,>	-	-	-50uA
	I/O Active Pull-down Current	V _{IL} (MAX) <v<sub>IN<v<sub>CCO, Pull Strength=Strong</v<sub></v<sub>	-	-	250uA
I _{PD}		V _{IL} (MAX) <v<sub>IN<v<sub>CCO, Pull Strength=Medium</v<sub></v<sub>	-	-	150uA
		V _{IL} (MAX) <v<sub>IN<v<sub>CCO, Pull Strength=Weak</v<sub></v<sub>	-	-	50uA
C1	I/O Capacitance		-	5pF	8pF
		V _{CCO} =3.3V, Hysteresis=ON	-	400mV	-
V _{HYST}	Hysteresis for Schmitt Trigger inputs	V _{CCO} =2.5V, Hysteresis=ON	-	200mV	-
	тпууст ттрисэ	V _{CCO} =1.8V, Hysteresis=ON	-	100mV	-

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Name	Description	Condition	Min.	Тур.	Max.
		V _{CCO} =1.5V, Hysteresis=ON	-	70mV	1
		V _{CCO} =1.2V, Hysteresis=ON	-	40mV	-

3.3.2 Static Current

Table 3-9 Static Current

Name	Description	LV/UV	Device	Typ. ^[1]
Icc	Core Current	LV	GW5AS-138	100 mA
Iccx	V _{CCX} current (VCCX=2.5V)	LV	GW5AS-138	9 mA
Iccio	I/O Bank current (V _{CCIO} =3.3V)	LV	GW5AS-138	5 mA
I _{CC_REG}	Static Current (Built-in Regulator)	LV	GW5AS-138	6 mA

Note!

[1] The test condition for the typical value is 25°C.

3.3.3 Recommended I/O Operating Conditions

Table 3-10 I/O Operating Conditions Recommended

Name	Output V _{CCI}	o (V)		Input V _{REF} (V)		
Name	Min.	Тур.	Max.	Min.	Тур.	Max.
LVTTL33	3.135	3.3	3.465	-	-	-
LVCMOS33	3.135	3.3	3.465	-	-	-
LVCMOS25	2.375	2.5	2.625	-	-	•
LVCMOS18	1.71	1.8	1.89	-	-	-
LVCMOS15	1.425	1.5	1.575	-	-	-
LVCMOS12	1.14	1.2	1.26	-	-	-
SSTL15	1.425	1.5	1.575	0.68	0.75	0.9
SSTL18_I	1.71	1.8	1.89	0.833	0.9	0.969
SSTL18_II	1.71	1.8	1.89	0.833	0.9	0.969
SSTL25_I	2.375	2.5	2.645	1.15	1.25	1.35
SSTL25_II	2.375	2.5	2.645	1.15	1.25	1.35
SSTL33_I	3.135	3.3	3.465	1.3	1.5	1.7
SSTL33_II	3.135	3.3	3.465	1.3	1.5	1.7
HSTL18_I	1.71	1.8	1.89	0.816	0.9	1.08
HSTL18_II	1.71	1.8	1.89	0.816	0.9	1.08
HSTL15	1.425	1.5	1.575	0.68	0.75	0.9
PCI33	3.135	3.3	3.465	-	-	-
LVPECL33E	3.135	3.3	3.465	-	-	-
MLVDS25E	2.375	2.5	2.625	-	-	-

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Name	Output V _{CCIO} (V)			Input V _{REF} (V)		
Name	Min.	Тур.	Max.	Min.	Тур.	Max.
BLVDS25E	2.375	2.5	2.625	-	-	-
RSDS25E	2.375	2.5	2.625	-	-	-
LVDS25E ¹	2.375	2.5	2.625	-	-	-
SSTL15D	1.425	1.5	1.575	-	-	-
SSTL18D_I	1.71	1.8	1.89	-	-	-
SSTL18D_II	1.71	1.8	1.89	-	-	-
SSTL25D_I	2.375	2.5	2.625	-	-	-
SSTL25D_II	2.375	2.5	2.625	-	-	-
SSTL33D_I	3.135	3.3	3.465	-	-	-
SSTL33D_II	3.135	3.3	3.465	-	-	-
HSTL15D	1.425	1.575	1.89	-	-	-
HSTL18D_I	1.71	1.8	1.89	-	-	-
HSTL18D_II	1.71	1.8	1.89	-	-	-

Note!

 V_{CCIO} of Banks with True LVDS is recommended to be set to 2.5 V.

3.3.4 Single ended I/O DC Characteristic

Table 3-11 Single-ended DC Characteristic

Name	V _{IL}		ViH		VoL	V _{OH}	I _{OL} [1]	I _{OH} ^[1]
Name	Min	Max	Min	Max	(Max)	(Min)	(mA)	(mA)
							4	-4
							8	-8
LVCMOS33	-0.3V	0.8V	2.0V	\/±0.3	0.4V	V _{CCO} -0.4V	12	-12
LVTTL33	-0.3 V	0.60	2.00	V _{CCO} +0.3			16	-16
							24	-24
					0.2V	V _{CCO} -0.2V	0.1	-0.1
							4	-4
					8	-8		
LVCMOS25	-0.3V	0.7V	1.7V	7V $V_{CCO}+0.3$ 0.4V $V_{CCO}-0.4V$	0.4V	V _{CCO} -0.4V	12	-12
LVCIVIO323	-0.3 V	0.7 V	1.7 V			16	-16	
							24	-24
					0.2V	V _{CCO} -0.2V	0.1	-0.1
							4	-4
							8	-8
LVCMOS18	-0.3V	0.35 x V _{CCO}	0.65 x V _{CCO}	V _{CCO} +0.3	0.4V	V _{CCO-} 0.4V	12	-12
					16	-16		
							24	-24

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Name	V _{IL}		V _{IH}		VoL	V _{OH}	loL ^[1]	I _{OH} ^[1]
name	Min	Max	Min	Max	(Max)	(Min)	(mA)	(mA)
					0.2V	V _{CCO} -0.2V	0.1	-0.1
							4	-4
					0.4V	\/ 0.4\/	8	-8
LVCMOS15	-0.3V	0.35 x V _{CCO}	0.65 x V _{CCO}	V _{CCO} +0.3	0.47	V _{CCO} -0.4V	12	-12
							16	-16
					0.2V	V _{CCO} -0.2V	0.1	-0.1
							4	-4
LVCMOS12	-0.3V	0.25 v.\/	0.65 x V _{CCO} V _C	V _{CCO} +0.3	0.4V	V _{CCO} -0.4V	8	-8
LVCIVIOS 12	-U.3V	0.35 x V _{CCO}		VCCO+0.3			12	-12
					0.2V	V _{CCO} -0.2V	0.1	-0.1
LVCMOS10	-0.3	0.35 x V _{CCO}	0.65 x V _{CCO}	1.1V	0.4V	V _{CCO} -0.4V	1.5	-0.5
PCI33	-0.3V	0.3 x V _{CCO}	0.5 x V _{CCO}	V _{CCO} +0.3	0.1x V _{CCO}	0.9 x V _{CCO}	1.5	-0.5
SSTL18_II	-0.3V	V _{REF} -0.125V	V _{REF} +0.125V	V _{CCO} +0.3	0.4V	V _{CCO-} 0.4V	13.4	-13.4
SSTL18_I	-0.3V	V _{REF} -0.125V	V _{REF} +0.125V	V _{CCO} +0.3	0.40V	V _{CCO} -0.40V	8	-8
SSTL15	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	V _{CCO} +0.3	0.40V	V _{CCO} -0.40V	13	-13
SSTL135	-0.3	V _{REF} -0.09V	V _{REF} +0.09V	V _{CCO} +0.3	0.40V	V _{CCO} -0.40V	13	-13
HSTL18_I	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	V _{CCO} +0.3	0.40V	V _{CCO} -0.40V	8	-8
HSTL18_II	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	V _{CCO} +0.3	0.40V	V _{CCO} -0.40V	16	-16
HSTL15_I	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	V _{CCO} +0.3	0.40V	V _{CCO} -0.40V	8	-8
HSTL15_II	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	V _{CCO} +0.3	0.40V	V _{CCO} -0.40V	16	-16
HSUL12	-0.3	V _{REF} -0.13V	V _{REF} + 0.13V	V _{CCO} +0.3	0.40	V _{CCO} -0.40V	0.1	-0.1

Note!

[1] The total DC current limit (sourced and sinked) of all IOs in the same bank: the total DC current of all IOs in the same bank shall not be greater than n*8mA, where n represents the number of IOs bonded out from a bank.

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3.3.5 Differential I/O DC Characteristic

Table 3-12 Differential I/O DC Characteristic

Name	Description	Conditions	Min.	Тур.	Max.	Unit
V_{INA}, V_{INB}	Input Voltage	TBD	-0.4		2.625	V
V _{CM}	Input Common Mode Voltage	Half the Sum of the Two Inputs	0.05		1.8	V
V _{THD}	Differential Input Threshold	Difference Between the Two Inputs	±100	± 350	±600	mV
I _{IN}	Input Current	Power On or Power Off			20	μA
V _{OH}	Output High Voltage for VOP or VOM	R _T = 100 Ω			1.675	V
V _{OL}	Output High Voltage for VOP or VOM	R _T = 100 Ω	0.7			V
V _{OD}	Output Voltage Differential	$(V_{OP} - V_{OM}), R_T = 100Ω$	250	350	600	mV
ΔV_{OD}	Change in VOD Between High and Low	TBD			50	mV
Vos	Output Voltage Offset	$(V_{OP} + V_{OM})/2$, $R_T = 100\Omega$	1.000	1.250	1.425	V
ΔV _{OS}	Change in VOS Between High and Low	TBD			50	mV
Is	Short-circuit current	V _{OD} = 0V two outputs shorted			12	mA

3.4 AC Switching Characteristics

3.4.1 CFU Switching Characteristics

Table 3-13 CFU Timing Parameters

Nama	Description	Speed G	Unit	
Name Description		Min	Max	Offic
t _{LUT4_CFU}	LUT4 delay	-	-	ns
t _{SR_CFU}	Set/Reset to Register output	-	-	ns
t _{CO_CFU}	Clock to Register output	-	-	ns

3.4.2 BSRAM Switching Characteristics

Table 3-14 BSRAM Timing Parameters

Name	Description	Speed Grade		Unit
Ivallie	Description	Min	Max	Offic
t _{COAD_BSRAM}	Clock to output from read address/data	-	-	ns
t _{COOR_BSRAM}	Clock to output from output register	-	-	ns

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3.4.3 DSP Switching Characteristics

Table 3-15 DSP Timing Parameters

Name	Description	Speed G	Unit	
Ivaille	Description	Min	Max	Offic
t _{COIR_DSP}	Clock to output from input register	-	-	ns
t _{COPR_DSP}	Clock to output from pipeline register	-	-	ns
t _{COOR_DSP}	Clock to output from output register	-	-	ns

3.4.4 Clock and I/O Switching Characteristic

Table 3-16 External Switching Characteristics

Name	Description	Device	-8		-7		Unit
ivaine	Description	Device	Min	Max	Min	Max	UIIIt
Pin-LUT-Pin Delay ⁽¹⁾	Pin(IOxA) to Pin(IOxB) delay	GW5AS-138	-	-	-	-	ns
T _{HCLKdly}	HCLK tree delay	GW5AS-138	-	-		-	ns
T _{GCLKdly}	GCLK tree delay	GW5AS-138	-	-	-	-	ns

3.4.5 On chip Oscillator Switching Characteristics

Table 3-17 On chip Oscillator Switching Characteristics

Name	Description	Min.	Тур.	Max.
	Output Frequency (0 to + 85° C)	199.5 MHz	210 MHz	220.5 MHz
f _{MAX}	Output Frequency (-40 to +100° C)	189 MHz	210 MHz	231 MHz
t _{DT}	Output Clock Duty Cycle	-	50%	-

3.4.6 PLL Switching Characteristics

Table 3-18 PLL Switching Characteristic

Device	Name	Min.	Max.
GW5AS-138	CLKIN	10 MHz	400 MHz
	PFD	10 MHz	400 MHz
	VCO	800 MHz	2 GHz
	CLKOUT	6.25MHz ^[1]	1 GHz

Note!

6.25MHz is the minimum frequency of CLKOUT in non-cascaded mode.

3.5 Configuration Interface Timing Specification

The GW5AS-138 devices support multiple GowinCONFIG modes: SSPI, MSPI, SERIAL and CPU. For further detailed information, please refer to <u>UG704</u>, <u>Arora V FPGA Products Programming and Configuration Guide</u>.

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4 Ordering Information

4.1 Part Name

Figure 4-1 Part Naming Examples-ES

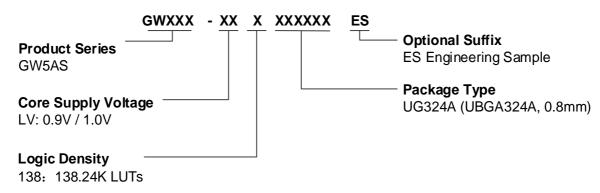
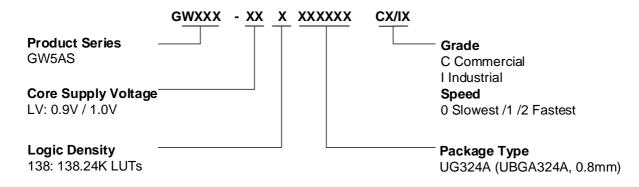


Figure 4-2 Part Naming Examples-Production



Note!

- For the further detailed information about the package information, please refer to 1.2 Product Resources.
- The LittleBee® family devices and Arora family devices of the same speed grade have different speeds.

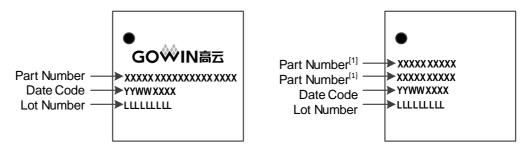
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• Both "C" and "I" are used in GOWIN part name marking for one device, such as C2/I1, C1/I0, etc. GOWIN devices are screened using industrial standards, so one same device can be used for both industrial (I) and commercial (C) applications. The maximum temperature of the industrial grade is 100°C, and the maximum temperature of the commercial grade is 85°C. Therefore, if the same chip meets the speed grade 2 in the commercial grade application, the speed grade is 1 in the industrial grade application.

4.2 Package Mark

The device information of GOWINSEMI is marked on the chip surface, as shown in Figure 4-3.

Figure 4-3 Package Mark Examples



Note!

[1] The first two lines in the right figure above are the "Part Number".

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5 About This Guide

5.1 Purpose

This data sheet describes the features, product resources, structure, AC/DC characteristics, and the ordering information of the GW5AS-138 devices, making it easier to understand the GW5AS-138 devices and select and use our devices.

5.2 Related Documents

The latest user guides are available on the GOWINSEMI Website. You can find the related documents at www.gowinsemi.com:

- <u>UG704, Arora V FPGA Products Programming and Configuration User Guide</u>
- UG1106, GW5AS-138 devices Package and Pinout Manual
- UG1107, GW5AS-138 Pinout

5.3 Terminology and Abbreviations

The terminology and abbreviations used in this manual are as shown in Table 5-1.

Table 5-1 Terminology and Abbreviations

Terminology and Abbreviations	Full Name
ADC	Analog to Digital Converter
AER	Advanced Error Reporting
ALU	Arithmetic Logic Unit
BSRAM	Block Static Random Access Memory
CFU	Configurable Function Unit
CLS	Configurable Logic Slice
CMSER	Configuration Memory Soft Error Recovery
CRU	Configurable Routing Unit
CSI	Camera Serial Interface
СТС	Clock Tolerance Compensation

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CTLE Continuous Time Linear Equation DCS Dynamic Clock Selector DFF D Flip-floor DNA Device Identifier DP True Dual Port 16K BSRAM	
DFF D Flip-floor DNA Device Identifier	1
DNA Device Identifier	1
	1
DD True Duel Port 16K BSDAM	1
The Dual Fort for BSNAW	
DSI Display Serial Interface	
DSP Digital Signal Processing	
ECC Error Correction Code	
ECRC End-to-End Cyclic Redunda	ancy Check
ESD Electro-Static Discharge	
FIFO First In First Out	
FPG FCPBGA	
FPGAs Field Programmable Gate A	Array
GCLK Global Clock	
GPIO Gowin Programmable IO	
GSR Global Set/Reset	
HCLK High Speed Clock	
IOB Input/Output Block	
LUT Look-up Table	
LW Long Wire	
MIPI Mobile Industry Processor I	nterface
OTP One Time Programmable	
PCIe Peripheral Component Inter	face Express
PCS Physical Coding Sublayer	
PLL Phase-locked Loop	
PMA Physical Medium Attachmen	nt Sublayer
REG Register	
SDP Semi Dual Port 16K BSRAM	M
SP Single Port 16K BSRAM	
SSRAM Shadow Static Random Acc	cess Memory
TDM Time Division Multiplexing	

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5.4 Support and Feedback

Gowin Semiconductor provides customers with comprehensive technical support. If you have any questions, comments, or suggestions, please feel free to contact us directly using the information provided below.

Website: www.gowinsemi.com
E-mail: support@gowinsemi.com

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Preliminary

